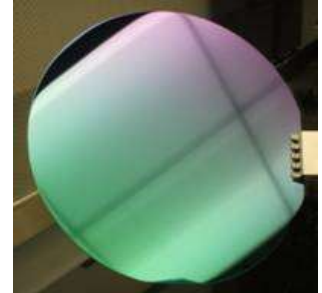


DATA SHEET – 2 INCH SILICON WAFER

Orientation

On standard:
(100) (111) (110)

On request:
(211) (311) (411) (511) (711) (911)
(210) (310) (510) (910)
(531) (731)



Standard Tolerance: $\pm 0.5^\circ$, on request: $\pm 0.02^\circ$

Type

P-type: Boron

N-type: Phosphorus, Arsenic, Antimony

Undoped

Resistivity

Cz: from 1m Ω .cm to 150 Ω .cm

FZ: up to 10k Ω .cm

Intrinsic: > 200 Ω .cm

General specifications

Standard Diameter: 2 inch (50.8mm) ± 0.1 mm

Standard Thickness: 275 μ m ± 25 μ m

Standard TTV: <10 μ m

TTV min SSP: 5 μ m

TTV min DSP: 5 μ m

Maximum Thickness: 10 mm

Particle count: 10 – 25

Bow: 30 μ m

Roughness: On polished surface: < 1nm

Flatness: On polished surface: < 1 μ m

Laser marking

On Request

DATA SHEET – 2 INCH SILICON WAFER

Thermal Oxidation

Oxidation type	Thickness	Tolerance
Wet oxidation	200 – 3000 nm	±10 %
Standard dry oxidation	15 – 100 nm	±5 %
High purity dry oxidation	20 – 350 nm	±5 %

Option: Single face oxidation (photolithography)

Single layer deposition / metallization

Layer	Method	Thickness	Tolerance
Cr, Ti, Au, Al, Pt, Mo, W	PVD	200 – 1000 nm Depending on metals	±10 %
Highly reflective silver coating	sputtering		
Ni, Cu, Ir, Ta, Al ₂ O ₃	evaporation		
Cr/Au TiW with Ti : 10% W : 90% TiW /Au with Ti : 10% W : 90% Ti/Pt	PVD		

Multi layers deposition

On Request

Example:

